

UNITED STATES PATENT APPLICATION

FOR

**METHOD OF FORMING HSQFN TYPE PACKAGE**

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## Field of the Invention

The present invention relates to a semiconductor package, and more specifically, to a method of forming HSQFN (High Stand-off Quad Flat Non-leaded) type package.

## Background of the Invention

Integrated circuits industry and fabrication involve the formation of semiconductor wafers, integrated circuits and chip package. With the advent of Ultra Large Scale Integrated (ULSI) circuits technologies, it has been a trend to scale down the geometry dimension of semiconductor devices and increase the density of semiconductor devices per unit area of silicon wafer. Thus, the sizes of devices, such as memory cells, have gotten smaller and smaller such that the area available for a single device has become very small. Further, the manufacturers of the devices are striving to reduce the sizes while simultaneously increasing their speed. The renewed interest in high density hybrid is driven by the requirement to handle large numbers of IC interconnections, the increasing clock rate of

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digital systems and the desire to pack greater functionality into smaller spaces. Therefore, the number of a package's leads becomes more and more. An issue is that the package must have the capability to  
5 spread the heat generated by the die, efficiently.

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10 For assembling a semiconductor device, a semiconductor chip is properly positioned against the lead frame thus formed, then attached to the insulating film by heat and pressure. Next, the inner leads and their corresponding contact pads are electrically connected by bonding wires using a bonding tool, respectively. Finally, the inner leads and the semiconductor chip are covered by a molding  
15 resin to expose the outer leads of the lead frame from the molding resin.

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20 United States Patent 6,118,173 to Emoto, entitled "Lead frame and a semiconductor device". The package includes a chip, inner leads reaches the periphery of the semiconductor chip, and bonding wires for electrically connecting the semiconductor chip and the inner leads. The semiconductor chip is fixed on a die pad portion, and a chip fixing inner  
25 lead is integrated with the die pad portion. To

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simplify the bonding wire connection process and improve the reliability, the chip fixing inner lead has a step portion so that the die pad portion is formed at a lower position than the inner leads.

5 Further, United States Patent 6,107,675 disclosed a lead frame structure.

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10 One of the package types is so called QFP (Quad flat package), the QFP is the type used in logic and microprocessor packing that requires up to approximately hundreds pins. The semiconductor memory devices are designed to terminals (leads) for external connection as short as possible in order to make it possible to operate the devices at a higher speed such as the QFN (Quad Flat Non-leaded package).  
15 The QFN has a high-speed-oriented package structure in which no leads are provided but electrode pads for soldering are provided to a resin package.

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### Summary of the Invention

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~~The object of the present invention is to provide a package with easier process and improved thermal dissipation.~~

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25 ~~A method of forming a HSQFN (High Stand-off Quad Flat Non-leaded) package comprising Providing a~~

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leadframe with bonding pads and die pads for receiving  
a die. Then, the die is attached on the die pad and  
bonding wires are connected between the bonding pads  
and the die for electrical connection. Molding  
5 process is used to encompass the die by compound from  
a first surface of the leadframe. Then, backside  
etching is used to the leadframe from a second surface  
of the leadframe to expose a lower surface of the  
compound, thereby separating the bonding pads and the  
10 die pads. A sigulation is applied to separate each  
individual package by cutting the leadframe and the  
compound.

Brief Description of the Drawings

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15 FIGURE 1 is a cross section view of a step of  
forming die pad and bonding pad according to the  
present invention.

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FIGURE 2 is a cross section view of a step of  
bonding die on a die pad according to the present  
invention.

FIGURE 3 is a cross section view of a step of  
bonding wires according to the present invention.

FIGURE 4 is a cross section view of a step of  
25 molding according to the present invention.

FIGURE 5 is a cross section view of a step of backside etching according to the present invention.

FIGURE 6 is a cross section view of a step of separating according to the present invention.

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### Detailed Description of the Preferred Embodiment

The present invention discloses a method for a High Stand-off Quad Flat Non-leaded package technology. A package in accordance with the invention will be described in conjunction with and illustrative embodiment of the invention. Please referring to FIGURE 6, the structure of the HSQFN (High Stand-off Quad Flat Non-leaded) includes a leadframe having a die pad 62 and bonding pads 60. The die pad 62 and bonding pads 60 are the portions of the leadframe. The several die pad 62 straightly elongated in parallel relationship to each other from the frame body. The die pad 62 is designed to carry the die 64 adhesived thereon by adhesive material 63. A number of bonding pads 60 formed on the lower surface of the package, and the die 66 is connected to the bonding pads 60 of the lead frame via a plurality of bonding wires 68 for electrical communication. Molding compound 70 encompasses the entire die 66, the bonding wire 68 and the major portion of the lead

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Station	Time	Lat	Long	Alt	Temp	Wind	Dir	Speed	Pressure	Humidity	Clouds	Remarks
101	0000	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
102	0100	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
103	0200	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
104	0300	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
105	0400	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
106	0500	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
107	0600	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
108	0700	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
109	0800	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
110	0900	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
111	1000	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
112	1100	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
113	1200	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
114	1300	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
115	1400	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
116	1500	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
117	1600	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
118	1700	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
119	1800	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
120	1900	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
121	2000	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
122	2100	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
123	2200	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear
124	2300	33° 45' N	150° 00' W	10	55.0	10	000	000	1010.0	85	000	Clear

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frame, leaving the terminal of the inner lead exposed out of the body. According to the structure of the present invention, not only the die pad is exposed, but also the lower surface of the bonding pad 60 is exposed. This structure provides excellent thermal dissipation from the packages.

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Two stages of etching are used to etch the upper surface (first side) and lower surface (second surface), respectively. The method comprises performing die bonding, wire bonding and molding between two stages of etching. Wherein a first etching of the two stages of etching comprises forming an inward indentation portion of the leadframe from a first side of said leadframe to define die pads and bonding pads. A second etching of the two stages of etching comprises separating the die pads and bonding pads by etching from a second side of the leadframe.

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20 The method for forming the package includes preparing a lead frame having a die pad 62 to receive a die 64, as shown in FIGURE 1. This present invention can be achieved by using "stand off" method. In one preferred embodiment, please refer to FIGURE 1, the upper surface (the first surface) of the lead frame

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[illegible]

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Turning to FIGURE 4, the die is encapsulated by mold resin 70. To phrase in another way, molding compound is injected into a mold to form a shielding to protect the die 64 from being damaged by external force. Please turn to FIGURE 5, thereafter, PMC (post molding curing) step is performed, this is well known in the art, detailed description is unnecessary. Next, a backside etch is utilized to separate the connection between the die pads 62 and the bonding pads 60. This can be achieved by using lithography and



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etching process to etch the leadframe from the second surface of the leadframe, thereby exposing the lower surface of the mold resin 70. Other method may be used, as shown in FIGURE 5. The etched portions of the 5 leadfram are aligned to the inward indentation portions of the first surface.

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Referring to FIGURE 6, a sigulation step is performed to separate each individual package. 10 Therefore, the package is cut at specific portions. Optionally, solder ball may be formed on the terminal of the bonding pads.

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The benefits of the present invention includes the improvement of heat dissipation characteristic. The die pad which is a portion of the leadfeame is exposed to enhance the thermal dissipation.

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As is understood by a person skilled in the art, the foregoing preferred embodiments of the present invention are illustrated of the present invention rather than limiting of the present invention. It is intended to cover various modifications and similar arrangements included within the spirit and scope of 25 the appended claims, the scope of which should be

accorded ~~the~~ broadest interpretation so as to encompass all such modifications and similar structure. Thus, while the preferred embodiment of the invention has been illustrated and described, it

5 will be appreciated that various changes can be made therein without departing from the spirit and scope of the invention.

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